

# STTB506B(-TR)

## TURBOSWITCH™ "B" . ULTRA-FAST HIGH VOLTAGE DIODE

#### MAIN PRODUCT CHARACTERISTICS

I <sub>F(AV)</sub>	5 A
V <sub>RRM</sub>	600 V
V <sub>F</sub> (max)	1.3 V
t <sub>rr</sub> (typ)	45 ns

#### FEATURES AND BENEFITS

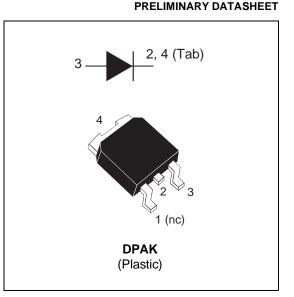
- SPECIFIC TO THE FOLLOWING OPERATIONS: SNUBBING OR CLAMPING, DEMAGNETIZA-TION AND RECTIFICATION, FREEWHEEL OR BOOSTER DIODE
- ULTRA-FAST RECOVERY
- VERY LOW OVERALL POWER LOSSES IN BOTH THE DIODE AND THE COMPANION TRANSISTOR
- DESIGNED FOR HIGH PULSED CURRENT OP-ERATIONS
- SURFACE MOUNT DEVICE
- TAPE AND REEL OPTION : -TR

#### DESCRIPTION

The TURBOSWITCH is a very high performance series of ultra-fast voltage power diodes from 600V to 1200V.

TURBOSWITCH "B" family drastically cuts losses in all high voltage operations which require extremely fast, soft and noise-free power diodes. They are particulary suitable in the primary circuit

#### ABSOLUTE MAXIMUM RATINGS



of an SMPS as snubber, clamping or demagnetizer diodes, and also in most power converters as high performance Rectifier diodes.

Packaged in DPAK Surface Mount enveloppe, these 600V devices are particulary intended for use on 240V domestic mains.

Symbol	Parameter	Value	Unit	
V <sub>RRM</sub>	Repetitive Peak Reverse Voltage	600	V	
V <sub>RSM</sub>	Non Repetitive Surge Reverse Voltage	600	V	
I <sub>F(RMS)</sub>	RMS Forward Current	8	А	
I <sub>FRM</sub>	Repetitive Peak Forward Current	tp = 5 μs F = 5 KHz	65	А
T <sub>stg</sub>	Storage Temperature Range	- 65 to + 150	°C	
Tj	Max. Junction Temperature	150	°C	

TM : TURBOSWITCH is a trademark from SGS-THOMSON Microelectronics.

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#### THERMAL AND POWER DATA

Symbol	Parameter	Conditions	Value	Unit
R <sub>th (j-c)</sub>	Junction to Case Thermal Resistance		TBD	°C/W
P <sub>1</sub>	Conduction Power Dissipation	$I_{F(AV)} = 1.5A, \ \delta = 0.5$ $T_L = °C$	TBD	W
P <sub>max</sub>	Total Power Dissipation $P_{max} = P_1 + P_3$ $(P_3 = 10\% P_1)$	T <sub>L</sub> = 76°C	TBD	°C/W

#### STATIC ELECTRICAL CHARACTERISTICS

Symbol	<b>Tests Conditions</b>	Tests Conditions		Min.	Тур.	Max.	Unit
I <sub>R</sub> *	Reverse leakage	Tj = 25°C	$V_R = 0.8 \text{ x } V_{RRM}$			100	μA
Current	Tj = 125°C				0.75	mA	
V <sub>F</sub> **	Forward Voltage	Tj = 25°C	I <sub>F</sub> = 5 A			1.4	V
drop	Tj = 125°C	I <sub>F</sub> = 5 A			1.3		

Pulse test : \* tp = 5 ms, duty cycle < 2 %

\*\* tp = 380  $\mu$ s, duty cycle < 2%

#### DYNAMIC ELECTRICAL CHARACTERISTICS

#### **TURN-OFF SWITCHING**

Symbol	Parameter	Test Conditions			Тур.	Max.	Unit
t <sub>rr</sub>	Reverse Recovery Time	Tj = 25℃	I <sub>F</sub> =0.5A I <sub>R</sub> =1A I <sub>rr</sub> =0.25A I <sub>F</sub> =1A dI <sub>F</sub> /dt=-50A/μs V <sub>R</sub> =30V		45	95	ns
t <sub>fr</sub>	Maximum Reverse Recovery Current	Tj = 125℃	$I_{F}=5A$ $V_{R}=400V$ $dI_{F}/dt = -40A/\mu s$ $dI_{F}/dt = -500A/\mu s$		20	7.5	A
S factor	Softness Factor	Tj = 125℃	V <sub>R</sub> =400V I <sub>F</sub> =5A dI <sub>F</sub> /dt = -500A/μs		1		/

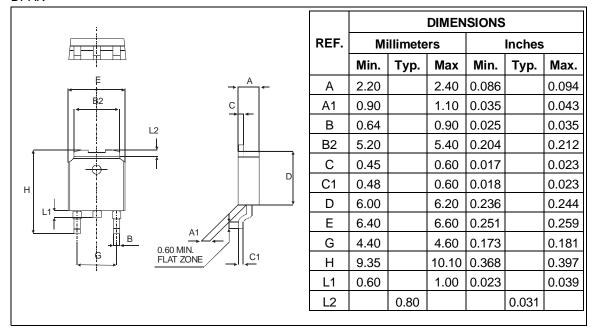
### **TURN-ON SWITCHING**

Symbol	Parameter	Test Conditions			Тур.	Max.	Unit
t <sub>rr</sub>	Forward Recovery Time	Tj = 25℃	I <sub>F</sub> =5A dI <sub>F</sub> /dt = 40A/μs Measured at 1.1 x V <sub>Fmax</sub>			500	ns
VPF	Peak Forward Voltage	Tj = 25℃	I <sub>F</sub> =5A dI <sub>F</sub> /dt = 40A/μs I <sub>F</sub> =25A dI <sub>F</sub> /dt=500A/μs		10	8	V

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#### PACKAGE MECHANICAL DATA DPAK



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